TS5A3359 1-Ω SP3T ANALOG SWITCH 5-V/3.3-V SINGLE-CHANNEL 3:1 MULTIPLEXER/DEMULTIPLEXER

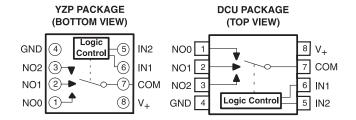
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FEATURES

- Isolation in Power-Down Mode, V₊ = 0
- Specified Break-Before-Make Switching
- Low ON-State Resistance (1 Ω)
- Control Inputs Are 5.5-V Tolerant
- Low Charge Injection
- Excellent ON-State Resistance Matching
- Low Total Harmonic Distortion (THD)
- 1.65-V to 5.5-V Single-Supply Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
 - 2000-V Human-Body Model (A114-B, Class II)
 - 1000-V Charged-Device Model (C101)

APPLICATIONS

- Cell Phones
- PDAs
- Portable Instrumentation
- Audio and Video Signal Routing
- Low-Voltage Data Acquisition Systems
- Communication Circuits
- Modems
- Hard Drives
- Computer Peripherals
- Wireless Terminals and Peripherals



FUNCTION TABLE

IN2	IN1	COM TO NO, NO TO COM
L	L	OFF
L	Н	COM = NO0
Н	L	COM = NO1
Н	Н	COM = NO2

DESCRIPTION/ORDERING INFORMATION

The TS5A3359 is a single-pole triple-throw (SP3T) analog switch that is designed to operate from 1.65 V to 5.5 V. The device offers a low ON-state resistance and excellent ON-state resistance matching with the break-before-make feature, to prevent signal distortion during the transferring of a signal from one channel to another. The device has an excellent total harmonic distortion (THD) performance and consumes very low power. These features make this device suitable for portable audio applications.

ORDERING INFORMATION

T _A	PACKAGE ⁽¹⁾⁽²⁾		ORDERABLE PART NUMBER	TOP-SIDE MARKING ⁽³⁾
–40°C to 85°C	NanoFree [™] – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)	Tape and reel	TS5A3359YZPR	J9_
	VSSOP - DCU	Tape and reel	TS5A3359DCUR	JAL_

- (1) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.
- (2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.
- (3) DCU: The actual top-side marking has one additional character that designates the assembly/test site. YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, = Pb-free).

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NanoFree is a trademark of Texas Instruments.



Summary of Characteristics⁽¹⁾

Configuration	Triple 3:1 Multiplexer/ Demultiplexer (1 × SP3T)				
Number of channels	1				
ON-state resistance (r _{on})	1.1 Ω				
ON-state resistance match (Δr _{on})	0.1 Ω				
ON-state resistance flatness (r _{on(flat)})	0.15 Ω				
Turn-on/turn-off time (t _{ON} /t _{OFF})	40 ns/35 ns				
Break-before-make time (t _{BBM})	1 ns				
Charge injection (Q _C)	40 pC				
Bandwidth (BW)	100 MHz				
OFF isolation (O _{ISO})	-65 dB at 10 MHz				
Crosstalk (X _{TALK})	-66 dB at 10 MHz				
Total harmonic distortion (THD)	0.01%				
Leakage current (I _{COM(OFF)} /I _{NO(OFF)})	±20 μA				
Power supply current (I ₊)	0.1 μΑ				
Package options	8-pin DCU or YZP				

(1) $V_+ = 5 \text{ V}, T_A = 25^{\circ}\text{C}$

ABSOLUTE MINIMUM AND MAXIMUM RATINGS(1)(2)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT	
V ₊	Supply voltage range ⁽³⁾		-0.5	6.5	V	
$V_{NO} \ V_{COM}$	Analog voltage range ⁽³⁾⁽⁴⁾⁽⁵⁾	-0.5	V ₊ + 0.5	V		
I _K	Analog port diode current	V _{NO} , V _{COM} < 0	-50		mA	
I _{NO}	On-state switch current	V V Oto V	-200	200	m ^	
I _{COM}	On-state switch current	V_{NO} , $V_{COM} = 0$ to V_{+}	-400	400	mA	
VI	Digital input voltage range (3)(4)		-0.5	6.5	V	
I _{IK}	Digital input clamp current	V _I < 0	-50		mA	
I ₊	Continuous current through V ₊			100	mA	
I _{GND}	Continuous current through GND			100	mA	
T _{stg}	Storage temperature range		-65	150	°C	

- (1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.
- (2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
- 3) All voltages are with respect to ground, unless otherwise specified.
- (4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (5) This value is limited to 5.5 V maximum.

PACKAGE THERMAL IMPEDANCE

				UNIT
θ_{JA}	Package thermal impedance ⁽¹⁾	DCU package	227	
	Package thermal impedance (*)	YZP package	140	°C/W

(1) The package thermal impedance is calculated in accordance with JESD 51-7.

ELECTRICAL CHARACTERISTICS FOR 5-V SUPPLY⁽¹⁾

 $V_{+} = 4.5 \text{ V}$ to 5.5 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST COI	NDITIONS	TA	V ₊	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V _{COM} , V _{NO}					0		V ₊	V
Peak ON resistance	r _{peak}	$0 \le (V_{NO}) \le V_{+},$ $I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 19	25°C Full	4.5 V		8.0	1.1 1.5	Ω
ON-state resistance	r _{on}	$V_{NO} = 2.5 \text{ V},$ $I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 19	25°C Full	4.5 V		0.7	0.9	Ω
ON-state				25°C			0.1	0.1	
resistance match between channels	Δr _{on}	$V_{NO} = 2.5 \text{ V},$ $I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 19	Full	4.5 V			0.1	Ω
ON-state		$0 \le (V_{NO}) \le V_{+},$ $I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 19	25°C			0.15		
resistance flatness	r _{on(flat)}	V _{NO} = 1 V, 1.5 V, 2.5	Switch ON,	25°C	4.5 V		0.1	0.25	Ω
namess		$I_{COM} = -100 \text{ mA},$	See Figure 19	Full				0.25	
	1	$V_{NO} = 1 \text{ V or } 4.5 \text{ V},$	Switch OFF,	25°C	5.5 V	-20	5	20	nA
NO OFF leakage	I _{NO(OFF)}	$V_{COM} = 1 \text{ V to } 4.5 \text{ V},$	See Figure 20	Full	3.5 V	-150		150	ПА
current	INO(DWDOEE)	$V_{NO} = 0 \text{ to } 5.5 \text{ V},$	Switch OFF,	25°C	0 V	-1	8.0		μA
	I _{NO(PWROFF)}	$V_{COM} = 5.5 \text{ V to } 0,$	See Figure 20	Full	- V	-25		25	μΑ
NO ON leakage		$V_{NO} = 1 \text{ V or } 4.5 \text{ V},$	Switch ON,	25°C	EEV	-30	5	30	~ ^
current	I _{NO(ON)}	V _{COM} = Open,	See Figure 20	Full	5.5 V	-220		220	nA
	1	$V_{NO} = 4.5 \text{ V or } 1 \text{ V},$	Switch OFF,	25°C	5.5 V	-25	8	25	nA
COM OFF leakage	I _{COM(OFF)}	$V_{COM} = 1 \text{ V or } 4.5 \text{ V},$	See Figure 20	Full	3.5 V	-250		250	ш
current	I _{COM(PWROFF)}	$V_{COM} = 0 \text{ to } 5.5 \text{ V},$	Switch OFF,	25°C	0 V	-8	0.1	8	μA
	COM(PWROFF)	$V_{NO} = 5.5 \text{ V to } 0,$	See Figure 20	Full	- V	-50		50	μπ
COM		V _{NO} = Open,	Switch ON,	25°C	EEV	-30	5	30	~ ^
ON leakage current	I _{COM(ON)}	$V_{COM} = 1 \text{ V or } 4.5 \text{ V},$	See Figure 20	Full	5.5 V	-220		220	nA
Digital Control	Inputs (IN1, IN	2) ⁽²⁾							
Input logic high	V _{IH}			Full		2.4		5.5	V
Input logic low	V_{IL}			Full		0		8.0	V
Input leakage	I _{IH} , I _{IL}	V _I = 5.5 V or 0		25°C	5.5 V	-2		2	uА
current	'IH, 'IL	v ₁ = 3.5 v 01 0		Full	J.J V	-20		20	

The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum All unused digital inputs of the device must be held at V_+ or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



ELECTRICAL CHARACTERISTICS FOR 5-V SUPPLY (continued)

 V_{+} = 4.5 V to 5.5 V, T_{A} = -40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CO	NDITIONS	TA	V ₊	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time		$V_{COM} = V_+,$	C _L = 35 pF,	25°C	5 V	1	2.5	21	ns
rum-on time	t _{ON}	$R_L = 50 \Omega$,	See Figure 23	Full	4.5 V to 5.5 V	1		23.5	115
Turn-off time	t	$V_{COM} = V_+,$	$C_L = 35 \text{ pF},$	25°C	5 V	1	6	10.5	ns
rum-on time	t _{OFF}	$R_L = 50 \Omega$,	See Figure 23	Full	4.5 V to 5.5 V	1		12	115
Break-before-	toou	$V_{NO} = V_{+}$	$C_L = 35 \text{ pF},$	25°C	5 V	0.5	8.5	18	ns
make time	t _{BBM}	$R_L = 50 \Omega$,	See Figure 24	Full	4.5 V to 5.5 V	0.5		23	113
Charge injection	Q_{C}	$V_{GEN} = 0,$ $R_{GEN} = 0,$	C _L = 1 nF, See Figure 28	25°C	5 V		20		pC
NO OFF capacitance	$C_{NO(OFF)}$	V _{NO} = V ₊ or GND, Switch OFF,	See Figure 22	25°C	5 V		18		pF
COM OFF capacitance	$C_{COM(OFF)}$	V _{COM} = V ₊ or GND, Switch OFF,	See Figure 22	25°C	2.5 V		54		pF
NO ON capacitance	C _{NO(ON)}	V _{NO} = V ₊ or GND, Switch ON,	See Figure 22	25°C	5 V		78		рF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 22	25°C	5 V		78		рF
Digital input capacitance	C _I	$V_I = V_+ \text{ or GND},$	See Figure 22	25°C	5 V		2.5		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 25	25°C	5 V		75		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, $f = 1 MHz$,	Switch OFF, See Figure 26	25°C	5 V		-64		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, $f = 1 MHz$,	Switch ON, See Figure 27	25°C	5 V		-64		dB
Total harmonic distortion	THD	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, See Figure 29	25°C	5 V		0.005		%
Supply				•	T.			,	
Positive supply		V V or CND	Switch ON or OFF	25°C	F. F. \/		16		~ ^
current	I ₊	$V_I = V_+ \text{ or GND},$	Switch ON or OFF	Full 5.5 V			1200	nA	

ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY⁽¹⁾

 $V_{+} = 3 \text{ V}$ to 3.6 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T _A	V ₊	MIN	TYP	MAX	UNIT
Analog Switch								,	
Analog signal range	V _{COM} , V _{NO}					0		V ₊	V
Peak ON resistance	r _{peak}	$0 \le (V_{NO}) \le V_{+},$ $I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 19	25°C Full	3 V		1.3	1.6	Ω
ON-state resistance	r _{on}	$V_{NO} = 2 V$, $I_{COM} = -100 \text{ mA}$,	Switch ON, See Figure 19	25°C Full	3 V		1.2	1.6 1.8	Ω
ON-state resistance match between channels	Δr _{on}	$V_{NO} = 2 \text{ V, } 0.8 \text{ V,}$ $I_{COM} = -100 \text{ mA,}$	Switch ON, See Figure 19	25°C Full	3 V		0.1	0.15	Ω
ON-state	_	$0 \le (V_{NO}) \le V_{+},$ $I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 19	25°C	0.1/		0.2		0
resistance flatness	r _{on(flat)}	$V_{NO} = 2 \text{ V}, 0.8 \text{ V},$ $I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 19	25°C Full	3 V		0.2	0.35	Ω
NO	I _{NO(OFF)}	V _{NO} = 1 V or 3 V, V _{COM} = 1 V to 3 V,	Switch OFF, See Figure 20	25°C Full	3.6 V	-15 -30	3	15 30	nA
OFF leakage current	I _{NO(PWROFF)}	$V_{NO} = 0 \text{ to } 3.6 \text{ V},$ $V_{COM} = 3.6 \text{ V to } 0,$	Switch OFF, See Figure 20	25°C	0 V	-1	0.2	1 10	μΑ
NO ON leakage	I _{NO(ON)}	V _{NO} = 1 V or 3 V,	Switch ON,	Full 25°C	3.6 V	-10 -15	3	15	nA
current	110(011)	$V_{COM} = Open,$ $V_{NO} = 0 V to 3.6 V,$	See Figure 20	Full 25°C		-40 -15	3	40 15	
COM OFF leakage	I _{COM(OFF)}	$V_{COM} = 1 \text{ V or}$ $V_{NO} = 3.6 \text{ V to 0},$ $V_{COM} = 3 \text{ V},$	Switch OFF, See Figure 20	Full	3.6 V	-75		75	nA
current	I _{COM(PWROFF)}	$V_{COM} = 0 \text{ to } 3.6 \text{ V},$ $V_{NO} = 3.6 \text{ V to } 0,$	Switch OFF, See Figure 20	25°C Full	0 V	-1 -20	0.2	1 20	μΑ
COM ON leakage current	I _{COM(ON)}	V _{NO} = Open, V _{COM} = 1 V or 3 V,	Switch ON, See Figure 20	25°C Full	3.6 V	-15 -40	4	15 40	nA
Digital Control	Inputs (IN1, IN	2) ⁽²⁾				1			
Input logic high	V _{IH}	-		Full		2		5.5	V
Input logic low	V _{IL}			Full		0		0.8	V
Input leakage current	I _{IH} , I _{IL}	V _I = 5.5 V or 0		25°C Full	3.6 V	-2 -20		20	nA

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

⁽²⁾ All unused digital inputs of the device must be held at V₊ or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY (continued)

 $V_{+} = 3 \text{ V to } 3.6 \text{ V}, T_{A} = -40^{\circ}\text{C} \text{ to } 85^{\circ}\text{C} \text{ (unless otherwise noted)}$

PARAMETER	SYMBOL	TEST CO	ONDITIONS	TA	V ₊	MIN	TYP MAX		UNIT
Dynamic				•					
Turn-on time	t _{ON}	$V_{COM} = V_+,$	$C_L = 35 pF,$	25°C	3.3 V	1	16	30.5	ns
rum on time	'ON	$R_L = 50 \Omega$,	See Figure 23	Full	3 V to 3.6 V	1		34	110
Turn-off time	t _{OFF}	$V_{COM} = V_+,$	$C_L = 35 pF$,	25°C	3.3 V	1	6	11.5	ns
ram on time	OFF	$R_L = 50 \Omega$,	See Figure 23	Full	3 V to 3.6 V	1		12.5	110
Break-before-	t _{BBM}	$V_{NO} = V_+,$	$C_L = 35 \text{ pF},$	25°C	3.3 V	0.5	13	26	ns
make time	-DDIVI	$R_L = 50 \Omega$,	See Figure 24	Full	3 V to 3.6 V	0.5		30	
Charge injection	$Q_{\mathbb{C}}$	$V_{GEN} = 0,$ $R_{GEN} = 0,$	C _L = 1 nF, See Figure 28	25°C	3.3 V		12		рС
NO OFF capacitance	$C_{NO(OFF)}$	V _{NO} = V ₊ or GND, Switch OFF,	See Figure 22	25°C	3.3 V		18		pF
COM OFF capacitance	C _{COM(OFF)}	V _{COM} = V ₊ or GND, Switch OFF,	See Figure 22	25°C	3.3 V		55		pF
NO ON capacitance	C _{NO(ON)}	V _{NO} = V ₊ or GND, Switch ON,	See Figure 22	25°C	3.3 V		78		pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 22	25°C	3.3 V		78		pF
Digital input capacitance	Cı	$V_I = V_+ \text{ or GND},$	See Figure 22	25°C	3.3 V		2.5		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 25	25°C	3.3 V		73		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, f = 1 MHz,	Switch OFF, See Figure 26	25°C	3.3 V		-64		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, f = 1 MHz,	Switch ON, See Figure 27	25°C	3.3 V		-64		dB
Total harmonic distortion	THD	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, See Figure 29	25°C	3.3 V		0.010		%
Supply									
Positive supply	l ₊	$V_1 = V_+$ or GND,	Switch ON or OFF	25°C	3.6 V		2	20	nA
current	1+	VI = V+ OI GIND,	SWILCH ON OF OFF	Full	3.0 V			350	IIA

ELECTRICAL CHARACTERISTICS FOR 2.5-V SUPPLY⁽¹⁾

 V_{+} = 2.3 V to 2.7 V, T_{A} = -40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CON	IDITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT	
Analog Switch										
Analog signal range	V_{COM}, V_{NO}					0		V ₊	٧	
Peak ON	r .	$0 \le (V_{NO}) \le V_+,$	Switch ON,	25°C	2.3 V		1.8	2.5	Ω	
resistance	r _{peak}	$I_{COM} = -8 \text{ mA},$	See Figure 19	Full	2.5 V			2.7	12	
ON-state	r _{on}	$V_{NO} = 1.8 V,$	Switch ON,	25°C	2.3 V		1.5	2	Ω	
resistance	on	$I_{COM} = -8 \text{ mA},$	See Figure 19	Full	2.0 V			2.4	32	
ON-state		V 4.0.V	Switch ON	25°C				0.2		
resistance match between channels	Δr_{on}	$V_{NO} = 1.8 \text{ V},$ $I_{COM} = -8 \text{ mA},$	Switch ON, See Figure 19	Full	2.3 V			0.2	Ω	
ON-state	_	$0 \le (V_{NO}) \le V_+,$ $I_{COM} = -8 \text{ mA},$	Switch ON, See Figure 19	25°C	227	0.6 2.3 V 0.6		0		
resistance flatness	r _{on(flat)}	$V_{NO} = 0.8 \text{ V}, 1.8 \text{ V}$	Switch ON,	25°C	2.3 V			Ω		
		$I_{COM} = -8 \text{ mA},$	See Figure 19	Full				1		
	I _{NO(OFF)}	$V_{NO} = 0$	$V_{NO} = 0.5 \text{ V or } 2.3 \text{ V},$	Switch OFF,	25°C	2.7 V	-15	3	15	nA
NO OFF leakage		$V_{COM} = 0.5 \text{ V to } 2.3 \text{ V},$	See Figure 20	Full		-30		30		
current	I _{NO(PWROFF)}	$V_{NO} = 0$ to 2.7 V,	Switch OFF,	25°C	0 V	-1	0.1	1	μΑ	
	-NO(FWROIT)	$V_{COM} = 2.7 \text{ V to 0},$	See Figure 20	Full		-10		10		
NO ON leakage	l	$V_{NO} = 0.5 \text{ V or } 2.3 \text{ V},$	Switch ON,	25°C	2.7 V	-15	3	15	nA	
current	I _{NO(ON)}	V _{COM} = Open,	See Figure 20	Full	Z.7 V	-35		35	ш	
		$V_{NO} = 0.3 \text{ V to } 2.3 \text{ V},$	Switch OFF,	25°C	2.7 V	-15	3	15	~ ^	
COM OFF leakage	I _{COM(OFF)}	$V_{COM} = 0.5 \text{ V or } 2.3 \text{ V},$	See Figure 20	Full	2.7 V	-60		60	nA	
current	1	$V_{COM} = 0 \text{ to } 2.7 \text{ V},$	Switch OFF,	25°C	0 V	-1	0.1	1	μΑ	
	I _{COM(PWROFF)}	$V_{NO} = 2.7 \text{ V to } 0,$	See Figure 20	Full	0 0	-10		10	μА	
COM		V _{NO} = Open,	Switch ON.	25°C	. = 1/	-15	3.5	15		
ON leakage current	I _{COM(ON)}	$V_{COM} = 0.5 \text{ V or } 2.2 \text{ V},$		Full	2.7 V	-40		40	nA	
Digital Control		2) ⁽²⁾				_		-		
Input logic high	V_{IH}			Full		1.8		5.5	V	
Input logic low	V_{IL}			Full		0		0.6	V	
Input leakage current	$I_{\rm IH},I_{\rm IL}$	V _I = 5.5 V or 0		25°C Full	2.7 V	10		10	nA	

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

⁽²⁾ All unused digital inputs of the device must be held at V₊ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.



ELECTRICAL CHARACTERISTICS FOR 2.5-V SUPPLY (continued)

 V_{+} = 2.3 V to 2.7 V, T_{A} = -40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CO	NDITIONS	TA	V ₊	MIN TYP MAX		MAX	UNIT
Dynamic									
Turn-on time	+	$V_{COM} = V_+,$	C _L = 35 pF,	25°C	2.5 V	2	4.5	43	ns
rum-on time	t _{ON}	$R_L = 50 \Omega$,	See Figure 23	Full	2.3 V to 2.7 V	2		47.5	115
Turn-off time	t	$V_{COM} = V_+,$	$C_L = 35 pF$,	25°C	2.5 V	2	8.5	11	ns
rum-on ume	t _{OFF}	$R_L = 50 \Omega$,	See Figure 23	Full	2.3 V to 2.7 V	2		12.5	115
Break-before-	t _{BBM}	$V_{NO} = V_+,$	$C_L = 35 pF$,	25°C	2.5 V	0.5	18.5	38.5	ns
make time	BBM	$R_L = 50 \Omega$,	See Figure 24	Full	2.3 V to 2.7 V	0.5		43	110
Charge injection	Q_{C}	$V_{GEN} = 0,$ $R_{GEN} = 0,$	C _L = 1 nF, See Figure 28	25°C	2.5 V		8		рС
NO OFF capacitance	$C_{NO(OFF)}$	V _{NO} = V ₊ or GND, Switch OFF,	See Figure 22	25°C	2.5 V		18.5		pF
COM OFF capacitance	$C_{\text{COM(OFF)}}$	V _{COM} = V ₊ or GND, Switch OFF,	See Figure 22	25°C	2.5 V		55		pF
NO ON capacitance	C _{NO(ON)}	V _{NO} = V ₊ or GND, Switch ON,	See Figure 22	25°C	2.5 V		78		pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 22	25°C	2.5 V		78		рF
Digital input capacitance	Cı	$V_I = V_+ \text{ or GND},$	See Figure 22	25°C	2.5 V		3		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 25	25°C	2.5 V		73		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, $f = 1 MHz$,	Switch OFF, See Figure 26	25°C	2.5 V		-64		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, f = 1 MHz,	Switch ON, See Figure 27	25°C	2.5 V		-64		dB
Total harmonic distortion	THD	$R_L = 600 \ \Omega,$ $C_L = 50 \ pF,$	f = 20 Hz to 20 kHz, See Figure 29	25°C	2.5 V		0.030		%
Supply								,	
Positive supply	1	$V_1 = V_+$ or GND,	Switch ON or OFF	25°C	2.7 V		1	10	nΛ
current	ent I_+ $V_I = V_+$ or GND,	$v_1 = v_+$ or GND,	Switch ON or OFF	Full	2.1 V	250			nA

ELECTRICAL CHARACTERISTICS FOR 1.8-V SUPPLY⁽¹⁾

 $V_{+} = 1.65 \text{ V}$ to 1.95 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CON	DITIONS	TA	V ₊	MIN	TYP	MAX	UNIT
Analog Switch	•								
Analog signal range	V _{COM} , V _{NO}					0		V ₊	V
Peak ON resistance	r _{peak}	$0 \le (V_{NO}) \le V_+,$ $I_{COM} = -2 \text{ mA},$	Switch ON, See Figure 19	25°C Full	1.65 V		5	30	Ω
ON-state resistance	r _{on}	$V_{NO} = 1.5 \text{ V},$ $I_{COM} = -2 \text{ mA},$	Switch ON, See Figure 19	25°C Full	1.65 V		2	2.5	Ω
ON-state		CON		25°C			0.15	0.4	
resistance match between channels	Δr_{on}	$V_{NO} = 1.5 \text{ V},$ $I_{COM} = -2 \text{ mA},$	Switch ON, See Figure 19	Full	1.65 V			0.4	Ω
ON-state		$0 \le (V_{NO}) \le V_+,$ $I_{COM} = -2 \text{ mA},$	Switch ON, See Figure 19	25°C			5		
resistance flatness	r _{on(flat)}	$V_{NO} = 0.6 \text{ V}, 1.5 \text{ V}$ $I_{COM} = -2 \text{ mA},$	Switch ON, See Figure 19	25°C Full	1.65 V		4.5 5		Ω
NO	I _{NO(OFF)}	V _{NO} =0.3 V or 1.65 V, V _{COM} = 0.3 V to 1.65 V,	Switch OFF, See Figure 20	25°C Full	1.95 V	–15 –30	3	15 30	nA
OFF leakage current	lua aura ann	$V_{NO} = 0$ to 1.95 V,	Switch OFF,	25°C	0.1/	-30 -1	0.1	1	
	I _{NO(PWROFF)}	$V_{COM} = 1.95 \text{ V to } 0,$	See Figure 20	Full	0 V	-15		15	μΑ
NO ON leakage current	I _{NO(ON)}	V _{NO} =0.3 V or 1.65 V, V _{COM} = Open,	Switch ON, See Figure 20	25°C Full	1.95 V	-15 -30	3	15 30	nA
	I _{COM(OFF)}	V _{NO} = 0.3 V to 1.65 V,	Switch OFF,	25°C	1.95 V	-15	3	15	nA
COM OFF leakage	-com(orr)	V _{COM} =0.3 V or 1.65 V,	See Figure 20	Full		-50		50	
current	I _{COM(PWROF} F)	$V_{COM} = 0 \text{ to } 1.95 \text{ V},$ $V_{NO} = 1.95 \text{ V to } 0,$	Switch OFF, See Figure 20	25°C Full	0 V	-1 -10	0.1	10	μΑ
COM ON leakage current	I _{COM(ON)}	V _{NO} = Open, V _{COM} = 0.3 V or 1.65 V,	Switch ON, See Figure 20	25°C Full	1.95 V	-15 -30	3	15 30	nA
Digital Control	Inputs (IN1. I	N2) ⁽²⁾							
Input logic high	V _{IH}	,		Full		1.5		5.5	V
Input logic low	V _{IL}			Full		0		0.6	V
Input leakage current	I _{IH} , I _{IL}	V _I = 5.5 V or 0		25°C Full	1.95 V	-2 -20		2 20	nA

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

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⁽²⁾ All unused digital inputs of the device must be held at V₊ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.



ELECTRICAL CHARACTERISTICS FOR 1.8-V SUPPLY (continued)

 V_{+} = 1.65 V to 1.95 V, T_{A} = -40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS			V ₊	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t _{ON}	$V_{COM} = V_+,$	$C_L = 35 \text{ pF},$	25°C	1.8 V	3	38.5	85	ns
Turr on time	ON	$R_L = 50 \Omega$,	See Figure 23	Full	1.65 V to 1.95 V	3		90	113
Turn-off time	t _{OFF}	$V_{COM} = V_+,$	$C_L = 35 \text{ pF},$	25°C	1.8 V	2	8.5	16	ns
ram on time	OFF	$R_L = 50 \Omega$,	See Figure 23	Full	1.65 V to 1.95 V	2		18	
Break-before-	t _{BBM}	$V_{NO} = V_+,$	$C_L = 35 \text{ pF},$	25°C	1.8 V	1	33	75	ns
make time	DDINI	$R_L = 50 \Omega$,	See Figure 24	Full	1.65 V to 1.95 V	1		80	_
Charge injection	$Q_{\mathbb{C}}$	$V_{GEN} = 0,$ $R_{GEN} = 0,$	C _L = 1 nF, See Figure 28	25°C	1.8 V		5		рC
NO OFF capacitance	$C_{NO(OFF)}$	V _{NO} = V ₊ or GND, Switch OFF,	See Figure 22	25°C	1.8 V		18.5		pF
COM OFF capacitance	C _{COM(OFF)}	V _{COM} = V ₊ or GND, Switch OFF,	See Figure 22	25°C	1.8 V		55		pF
NO ON capacitance	C _{NO(ON)}	V _{NO} = V ₊ or GND, Switch ON,	See Figure 22	25°C	1.8 V		78		pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 22	25°C	1.8 V		78		pF
Digital input capacitance	C _I	$V_I = V_+ \text{ or GND},$	See Figure 22	25°C	1.8 V		3		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 25	25°C	1.8 V		73		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega,$ f = 1 M Hz,	Switch OFF, See Figure 26	25°C	1.8 V		-64		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, f = 1 MHz,	Switch ON, See Figure 27	25°C	1.8 V		-64		dB
Total harmonic distortion	THD	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, See Figure 29	25°C	1.8 V		0.080		%
Supply									
Positive supply	ı	$V_1 = V_+$ or GND,	Switch ON or OFF	25°C	1.95 V		1		nA
current	I ₊	$V_1 = V_+ \cup I \cup \cup \cup$	SWILCTI ON OF OFF	Full	1.95 V	200			ΠA

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TYPICAL PERFORMANCE

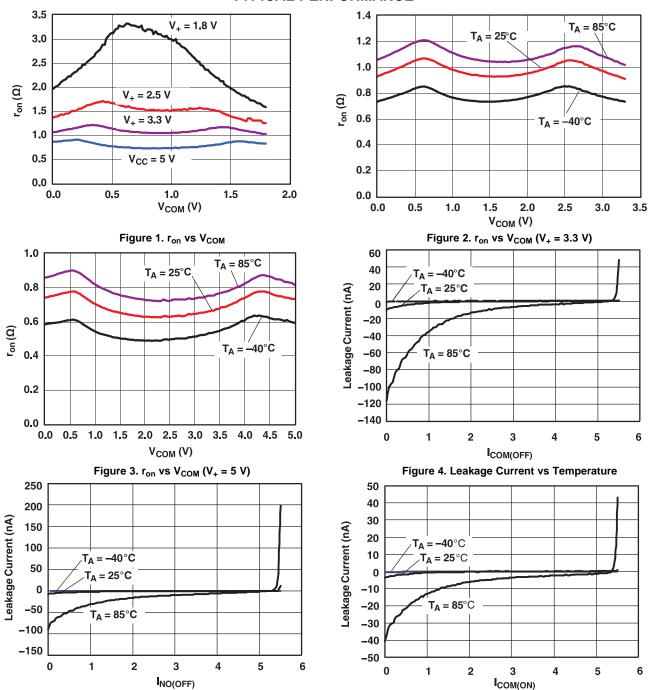


Figure 5. Leakage Current vs Temperature

Figure 6. Leakage Current vs Temperature



TYPICAL PERFORMANCE (continued)

14

12

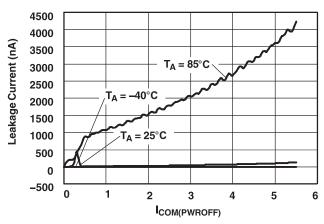
6 4

2

0

-40

ton/toff (ns) 8



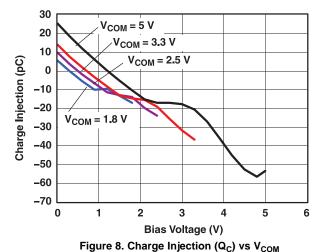


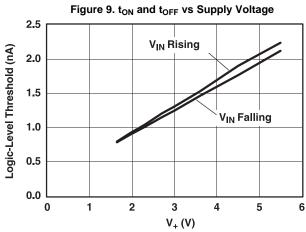
Figure 7. Leakage Current vs Temperature 90 80 toff 70 t_{ON}/t_{OFF} (ns) 20 20 09 09 60 ton 20 10 0 0 3 V_{CC} (V)

 t_{ON}

25

toff

85



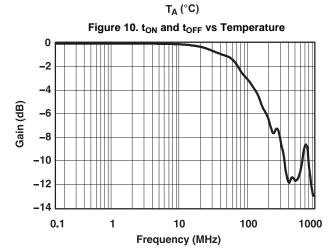
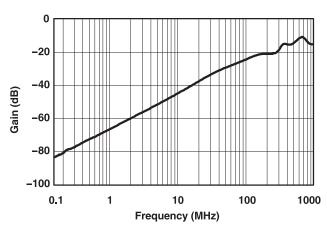


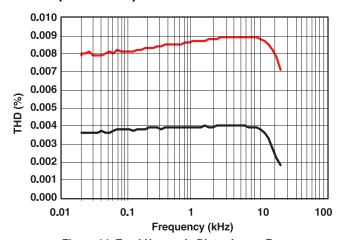
Figure 11. Logic-Level Threshold vs V₊

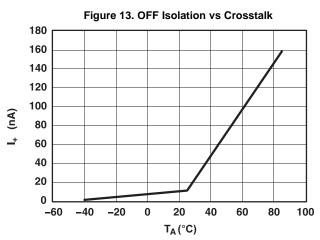
Figure 12. Bandwidth $(V_{+} = 5 \text{ V})$



TYPICAL PERFORMANCE (continued)







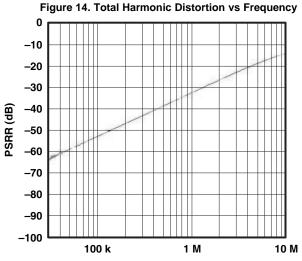
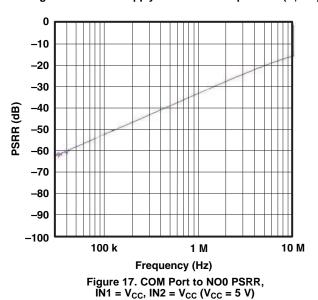
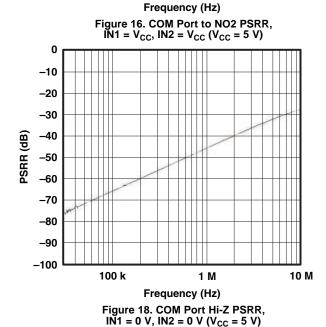


Figure 15. Power-Supply Current vs Temperature ($V_{+} = 5$)







PIN DESCRIPTION

PIN NO.	NAME	DESCRIPTION
1	NO0	Normally open
2	NO1	Normally open
3	NO2	Normally open
4	GND	Digital ground
5	IN2	Digital control to connect COM to NO
6	IN1	Digital control to connect COM to NO
7	COM	Common
8	V ₊	Power supply

PARAMETER DESCRIPTION

SYMBOL	DESCRIPTION
V _{COM}	Voltage at COM
V _{NO}	Voltage at NO
r _{on}	Resistance between COM and NC or COM and NO ports when the channel is ON
r _{peak}	Peak on-state resistance over a specified voltage range
Δr_{on}	Difference of ron between channels in a specific device
r _{on(flat)}	Difference between the maximum and minimum value of ron in a channel over the specified range of conditions
I _{NO(OFF)}	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state
I _{NO(PWROFF)}	Leakage current measured at the NO port during the power-down condition, $V_{+} = 0$.
I _{NO(ON)}	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the ON state and the output (COM) open
I _{COM(ON)}	Leakage current measured at the COM port, with the corresponding channel (COM to NO or COM to NC) in the ON state and the output (NC or NO) open
I _{COM(OFF)}	Leakage current measured at the COM port during the power-down condition, $V_{+} = 0$
I _{COM(PWROFF)}	Leakage current measured at the COM port during the power-down condition, $V_{+} = 0$.
V_{IH}	Minimum input voltage for logic high for the control input (IN)
V_{IL}	Maximum input voltage for logic low for the control input (IN)
V_{I}	Voltage at the control input (IN)
$I_{\rm IH},~I_{\rm IL}$	Leakage current measured at the control input (IN)
t _{ON}	Turn-on time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM or NO) signal when the switch is turning ON.
t_{OFF}	Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM or NO) signal when the switch is turning OFF.
t _{BBM}	Break-before-make time. This parameter is measured under the specified range of conditions and by the propagation delay between the output of two adjacent analog channels (NC and NO) when the control signal changes state.
Q _C	Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NO or COM) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, $Q_C = C_L \times \Delta V_{COM}$, C_L is the load capacitance and ΔV_{COM} is the change in analog output voltage.
$C_{NO(OFF)}$	Capacitance at the NO port when the corresponding channel (NO to COM) is OFF
$C_{NO(ON)}$	Capacitance at the NO port when the corresponding channel (NO to COM) is ON
$C_{COM(ON)}$	Capacitance at the COM port when the corresponding channel (COM to NO) is ON
$C_{COM(OFF)}$	Capacitance at the COM port when the corresponding channel (COM to NO) is OFF
C _I	Capacitance of control input (IN)
O _{ISO}	OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM or NO to COM) in the OFF state.
X _{TALK}	Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC to NO or NO to NC). This is measured in a specific frequency and in dB.
BW	Bandwidth of the switch. This is the frequency in which the gain of an ON channel is –3 dB below the DC gain.



TS5A3359 1-Ω SP3T ANALOG SWITCH 5-V/3.3-V SINGLE-CHANNEL 3:1 MULTIPLEXER/DEMULTIPLEXER

SCDS214C-OCTOBER 2005-REVISED JANUARY 2008

PARAMETER DESCRIPTION (continued)

SYMBOL	DESCRIPTION
THD	Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.
l ₊	Static power-supply current with the control (IN) pin at V ₊ or GND

Product Folder Link(s): TS5A3359



PARAMETER MEASURMENT INFORMATION

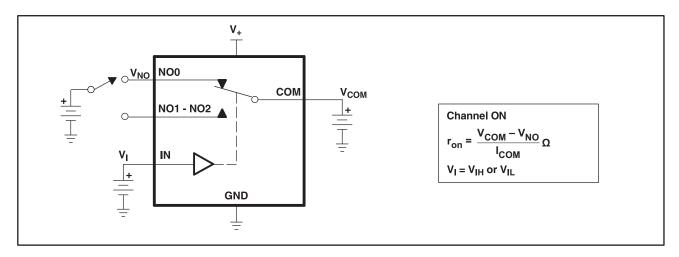
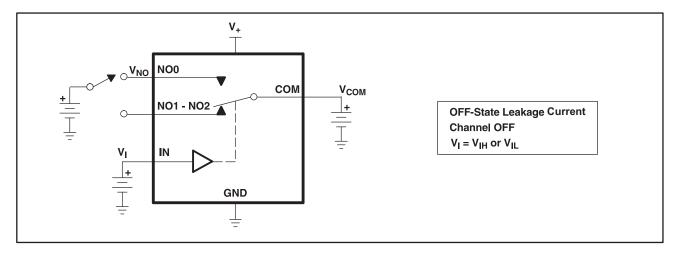


Figure 19. ON-State Resistance (ron)



 $\textbf{Figure 20. OFF-State Leakage Current (I}_{NC(OFF)}, I_{NO(OFF)}, I_{NO(PWROFF)}, I_{COM(OFF)}, I_{COM(PWROFF)})\\$

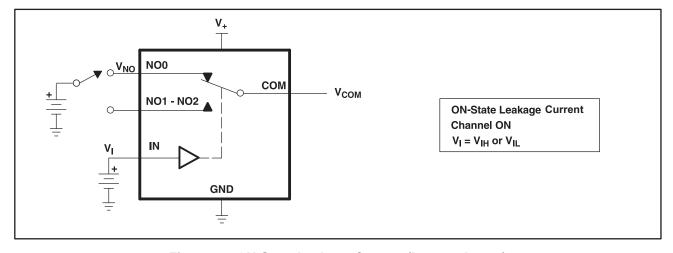


Figure 21. ON-State Leakage Current (I_{COM(ON)}, I_{NO(ON)})





PARAMETER MEASURMENT INFORMATION (continued)

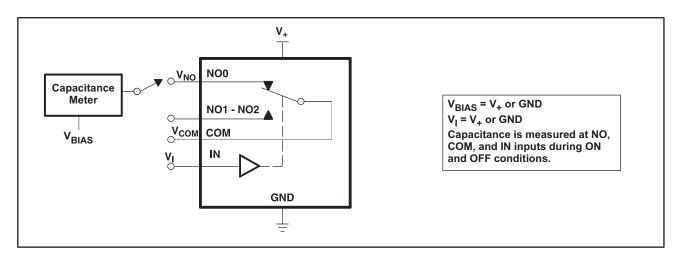
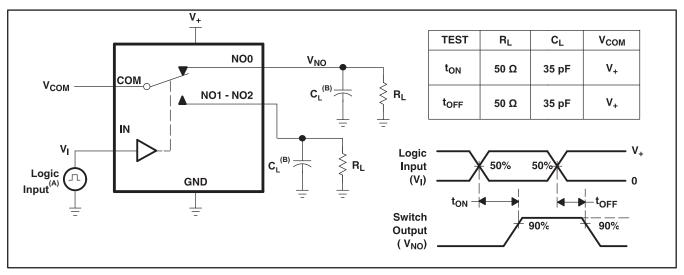


Figure 22. Capacitance (C_I, C_{COM(ON)}, C_{NO(OFF)}, C_{COM(OFF)}, C_{NO(ON)})

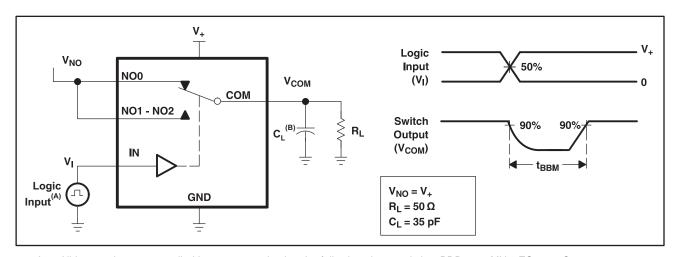


- A. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, ZO = 50 Ω , $t_r < 5$ ns, $t_f < 5$ ns.
- B. C_L includes probe and jig capacitance.

Figure 23. Turn-On (t_{ON}) and Turn-Off Time (t_{OFF})



PARAMETER MEASURMENT INFORMATION (continued)



- A. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, ZO = 50 Ω , $t_r < 5$ ns, $t_f < 5$ ns.
- B. C_L includes probe and jig capacitance.

Figure 24. Break-Before-Make Time (t_{BBM})

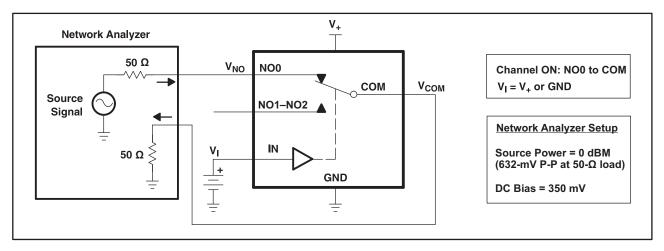


Figure 25. Bandwidth (BW)



PARAMETER MEASURMENT INFORMATION (continued)

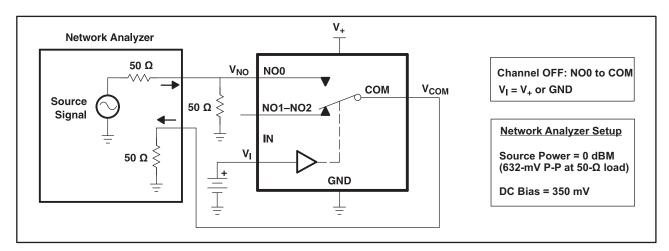


Figure 26. OFF Isolation (O_{ISO})

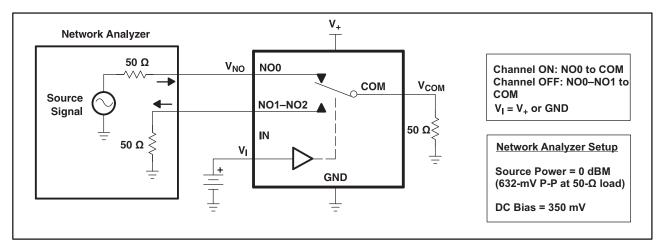
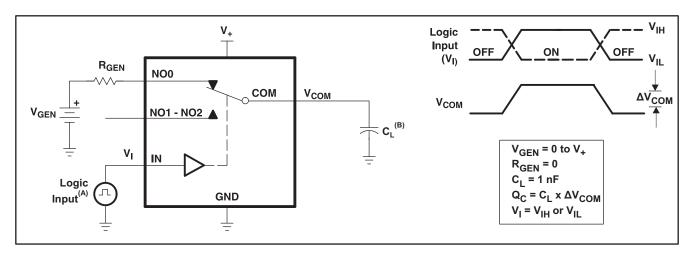


Figure 27. Crosstalk (X_{TALK})

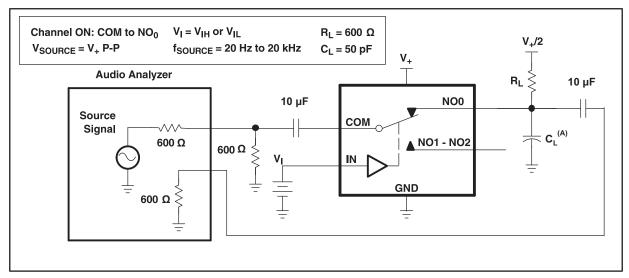


PARAMETER MEASURMENT INFORMATION (continued)



- A. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, ZO = 50 Ω , $t_r < 5$ ns, $t_f < 5$ ns.
- B. C_L includes probe and jig capacitance.

Figure 28. Charge Injection (Q_C)



A. C_L includes probe and jig capacitance.

Figure 29. Total Harmonic Distortion (THD)



PACKAGE OPTION ADDENDUM

1-Sep-2014

PACKAGING INFORMATION

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Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish (6)	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TS5A3359DCUR	ACTIVE	US8	DCU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	(AL ~ JALR) JZ	Samples
TS5A3359DCURG4	ACTIVE	US8	DCU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	(AL ~ JALR) JZ	Samples
TS5A3359DCUT	ACTIVE	US8	DCU	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	(AL ~ JALR) JZ	Samples
TS5A3359DCUTG4	ACTIVE	US8	DCU	8	250	TBD	Call TI	Call TI	-40 to 85	(AL ~ JALR) JZ	Samples
TS5A3359YZPR	ACTIVE	DSBGA	YZP	8	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(J9 ~ J97)	Samples
TS5A3359YZPRB	OBSOLETE	DSBGA	YZP	8		TBD	Call TI	Call TI		J97	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



PACKAGE OPTION ADDENDUM

1-Sep-2014

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS5A3359DCUR	US8	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
TS5A3359YZPR	DSBGA	YZP	8	3000	180.0	8.4	1.02	2.02	0.63	4.0	8.0	Q1

www.ti.com 6-Dec-2014



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS5A3359DCUR	US8	DCU	8	3000	202.0	201.0	28.0
TS5A3359YZPR	DSBGA	YZP	8	3000	210.0	185.0	35.0

DCU (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



NOTES:

- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
 - D. Falls within JEDEC MO-187 variation CA.



DCU (S-PDSO-G8)

PLASTIC SMALL OUTLINE PACKAGE (DIE DOWN)



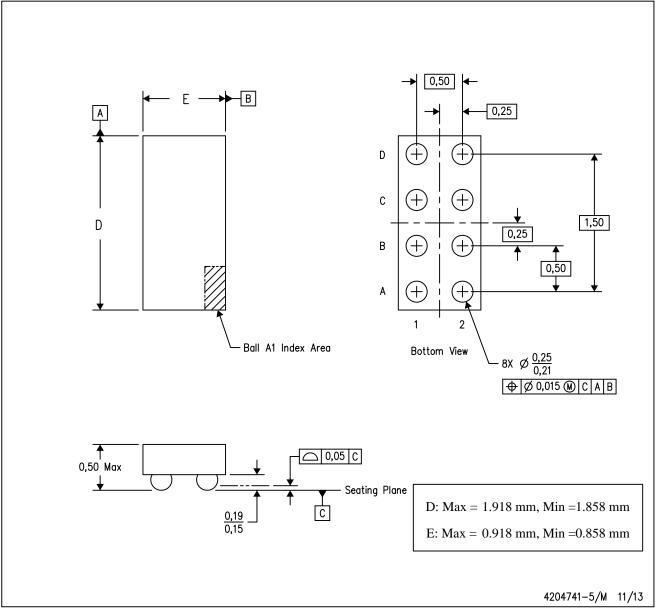
NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



YZP (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.

NanoFree is a trademark of Texas Instruments.



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